

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

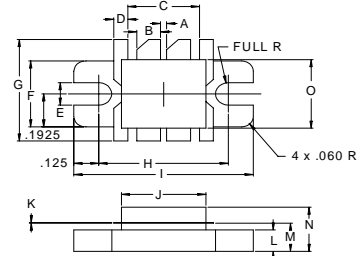
The **ASI BLV57** is Designed for use as push-pull amplifier, primarily in linear UHF TV transmitting Applications.

**FEATURES:**

- Input Matching Network
- Common emitter
- **Omnigold™** Metalization System with eutectic die bonding

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	2.0 A
<b>V<sub>CESM</sub></b>	50 V
<b>V<sub>CE</sub></b>	27 V
<b>P<sub>DISS</sub></b>	77 W @ T <sub>C</sub> = 25 C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	2.27 °C/W

**PACKAGE STYLE .400 8L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.030 / 0.76
B	.115 / 2.92	.125 / 3.18
C		.360 / 9.14
D	.065 / 1.65	.075 / 1.91
E		.130 / 3.30
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

**ORDER CODE: ASI10646**
**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 25 mA	27			V
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 10 mA	50			V
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 5.0 mA	3.5			V
<b>I<sub>CES</sub></b>	V <sub>E</sub> = 27 V			10	mA
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 25 V    I <sub>C</sub> = 850 mA	15			---
<b>f<sub>T</sub></b>	V <sub>CB</sub> = 25 V    I <sub>E</sub> = 1.7 A		2.5		GHz
	V <sub>CB</sub> = 25 V    I <sub>E</sub> = 850 mA		2.5		
<b>P<sub>G</sub></b> <b>IMD<sub>1</sub></b>	V <sub>CE</sub> = 25 V    I <sub>C</sub> = 850 mA    f = 860 MHz P <sub>OUT</sub> = 6.0 W	8.0 -60			dB dBc